

NSH020N06P5

N-Channel Enhanced Shielded Gate Trench Power MOSFET



Voltage: 60 Volts

Current: 170 Ampers

Polarity And Marking

Package: PDFN5*6

Features

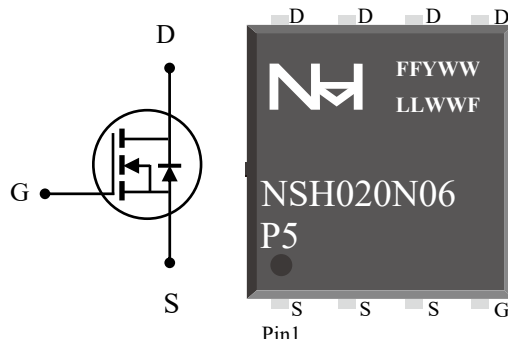
- NH'S Advanced SGT Technology
- Low Reverse Transfer Capacitances
- Low Gate Charge For Low Switching Loss
- Excellent $Q_g \cdot R_{ds(on)}$ Product(FOM)

Typical Applications

- Synchronous Rectification
- High-Frequency Circuits
- The Motor Drives
- Automotive Electronics
- Weight: App. 0.087 Grams (0.13403 Ounce)

Product Summary

V _{DS} Min.@T _j	60	V
I _D Min.@T _a	170	A
R _{DS(ON)} Typ.@10V	2	mΩ



Remark:

- ①. NH=Niuhang Trademark
- ②. FF=Product Line Code, According To Actual Changes
YWW=Date Code, According To Actual Changes
LLWWF=Internal Code, According To Actual Changes
- ③. NSH020N06P5=Model

***100% UIS TESTED**

***100% ΔV_{DS} TESTED**

Absolute Maximum Ratings (T_a=25°C Unless Otherwise Specified)

Parameter	Test Conditions	Symbol	Ratings	Unit
Drain-Source Voltage		V _{DS}	60	V
Gate-Source Voltage		V _{GS}	±20	V
Continuous Drain Current (Note 1)	T _a = 25 °C	I _D	170	A
	T _a = 100 °C		109	
Drain Current-Pulse (Note 1)	T _j < 150 °C	I _{DM}	680	A
Maximum Power Dissipation Power Dissipation Derating Factor Above 25°C	T _a = 25 °C	P _D	119	W
	T _a = 100 °C		48	
Derating Factor		D _F	0.95	W/°C
Avalanche Current, Single Pulse (Note 1)	L= 0.5 mH	I _{AS}	51.0	A
Single Pulse Avalanche Energy (Note 1) Test Circuit & Waveform See Fig.16	L= 0.5 mH I _{AS} = 51.0 A, R _G = 10.0 Ω Starting T _j =25 °C, V _G = 10.0 V	E _{AS}	650	mJ

Thermal Characteristics (T_a=25°C Unless Otherwise Specified)

Parameter	Test Conditions	Symbol	Typ.	Unit
Junction Temperature		T _J	-55 to 150	°C
Storage Temperature Range		T _{STD}	-55 to 150	°C
Thermal Resistance Junction To Ambient With Steady-State	Still Air Environment With T _a =25 °C	R _{θJA}	52.0	°C/W
Thermal Resistance Junction-Case With Steady-State	Device Mounted On 1 in2 FR-4 Board With 2oz. Copper	R _{θJC}	1.05	

Notes: 1. Pulse Width Limited By Max. Junction Temperature. (See Fig. 13).

NSH020N06P5
N-Channel Enhanced Shielded Gate Trench Power MOSFET

Electrical Characteristics (Ta=25°C Unless Otherwise Specified)

Parameter	Test Conditions	Symbol	Min.	Typ.	Max.	Unit
Static Off Characteristics						
Drain-Source Breakdown Voltage	VGS=0V,ID=250uA	BV _{DSS}	60	--	--	V
Bvdss Temperature Coefficient	ID=250uA,Reference25℃	ΔBV _{DSS} /ΔT _J	--	0.07	--	V/℃
Drain-Source Leakage Current	VDS= 60 V,VGS=0V	I _{DSS}	--	--	1	uA
Gate-Body Leakage Current	VGS= ±20 V,VDS=0V	I _{GSS}	--	--	±100	nA
Forward Transconductance	ID= 20.0 A,VDS= 5 V	g _{fs}	--	7.0	--	S
Static On Characteristics						
Gate Threshold Voltage	VGS= VDS ID=250uA	V _{GS(TH)}	2.0	3.0	4.0	V
Drain-Source On Resistance	ID= 20.0 A,VGS= 10.0 V	R _{DS(ON)}	--	2.0	2.4	mΩ
	ID= 20.0 A,VGS= 4.5 V		--	2.30	3.22	
Dynamic Characteristics						
Gate Resistance	VGS=0V,VDS=0V, Freq.=1MHz	R _g	--	2.0	--	Ω
Input Capacitance	VDS= 30 V	C _{iss}	--	4400.0	--	pF
Output Capacitance	VGS= 0 V	C _{oss}	--	1500.0	--	pF
Reverse Transfer Capacitance	F= 1 MHZ	C _{rss}	--	34.0	--	pF
Switching Paramters (Test Circuit & Waveform See Fig.14)						
Turn-On Delay Time	VDS= 30 V	t _{d(on)}	--	20.0	--	ns
Turn-On Rise Time	VGS= 10.0 V	t _r	--	15.0	--	ns
Turn-Off Delay Time	RG= 10.0 Ω	t _{d(off)}	--	75.0	--	ns
Turn-Off Rise Time		t _f	--	20.0	--	ns
Gate Charge Paramters (Test Circuit & Waveform See Fig.15)						
Total Gate Charge	VDS= 30 V	Q _g	--	94.0	--	nC
Gate-Source Charge	VGS= 10.0 V	Q _{gs}	--	15.0	--	nC
Gate-Drain Charge	ID= 20.0 A	Q _{gd}	--	12.0	--	nC
Drain-Source Diode Characteristics And Maximum Ratings (Test Circuit & Waveform See Fig.17)						
Max. Diode Forward Cuurent		I _S	--	--	170	A
Max. Pulsed Forward Cuurent		I _{SM}	--	--	595	A
Diode Forward Voltage	ID= 20.0 A,VGS=0V	V _{SD}	--	0.85	1.2	V
Reverse Recovery Time	ID= 20.0 A,di/dt= 100 A/us	t _{rr}	--	66.0	--	ns
Reverse Recovery Charge	VGS= 10.0 V,VDD= 30 V	Q _{rr}	--	80.0	--	nC

NSH020N06P5

N-Channel Enhanced Shielded Gate Trench Power MOSFET



Typical Characteristics Curves

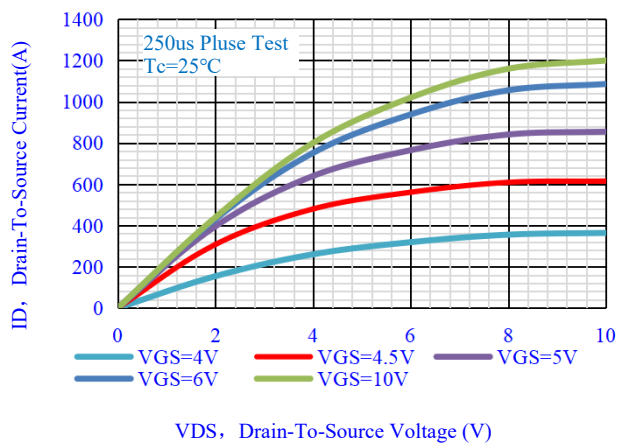


Fig.1-Output Characteristics

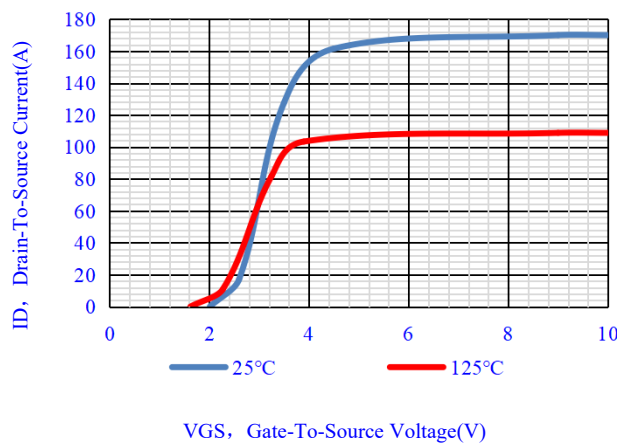


Fig.2- Transfer Characteristics

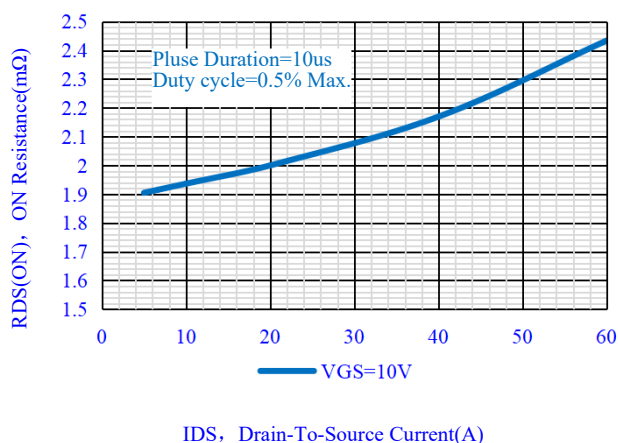


Fig.3- On Resistance vs. Drain Current

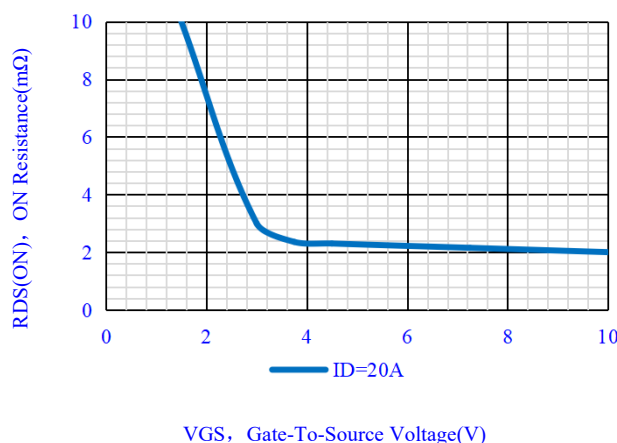


Fig.4- On Resistance vs. Gate Source Voltage

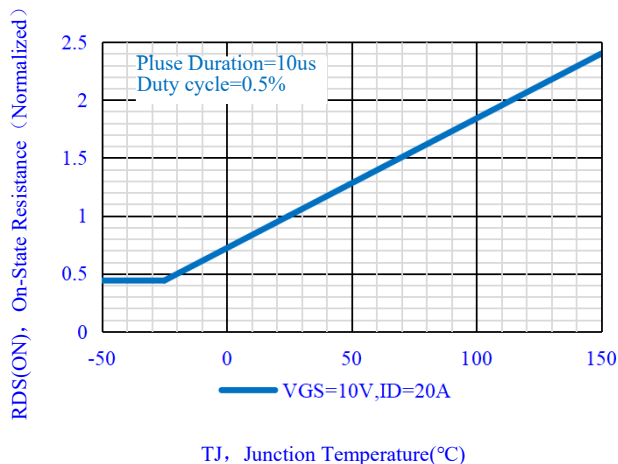


Fig.5- On Resistance vs. Junction Temperature

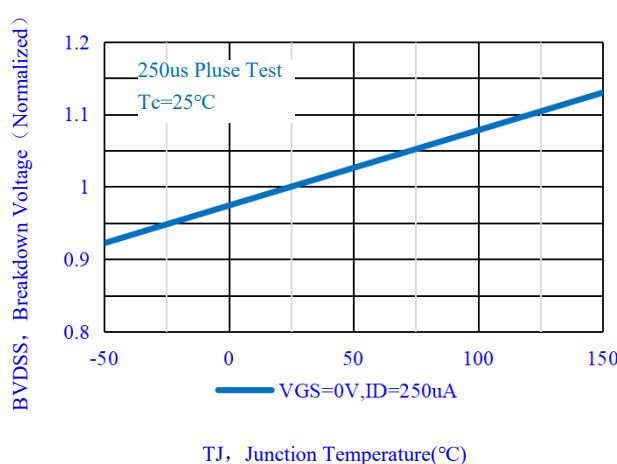


Fig.6- Breakdown Voltage vs. Junction Temperature

NSH020N06P5

N-Channel Enhanced Shielded Gate Trench Power MOSFET



Typical Characteristics Curves

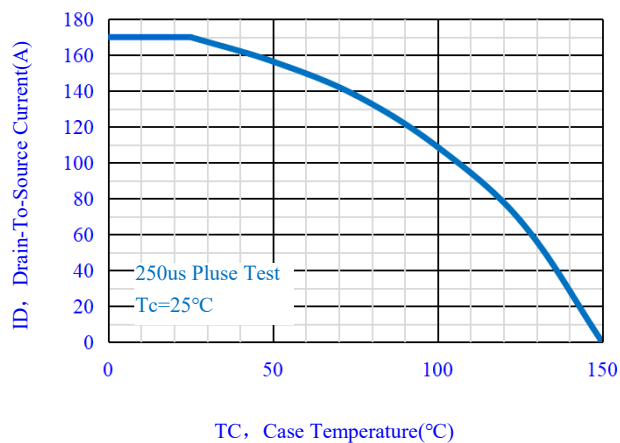


Fig.7-Maximum Continuous Drain Current vs. Case Temperature

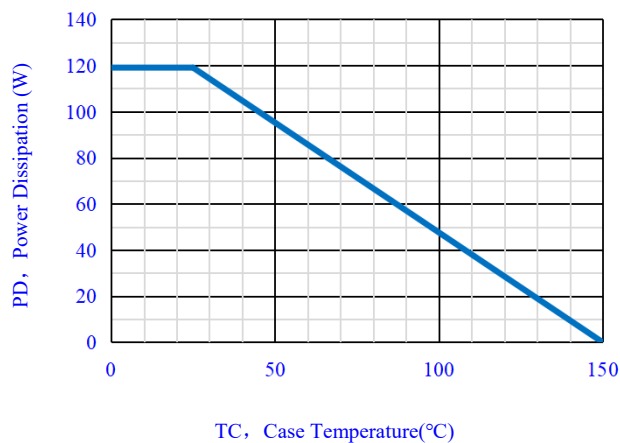


Fig.8-Maximum Power Dissipation vs. Case Temperature

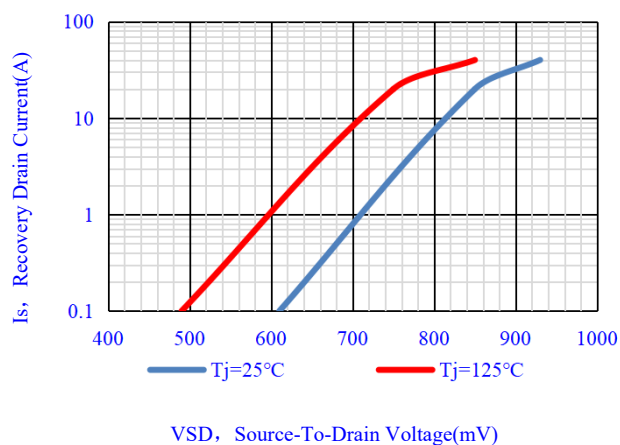


Fig.9- Source-To-Drain Diode Forward Voltage

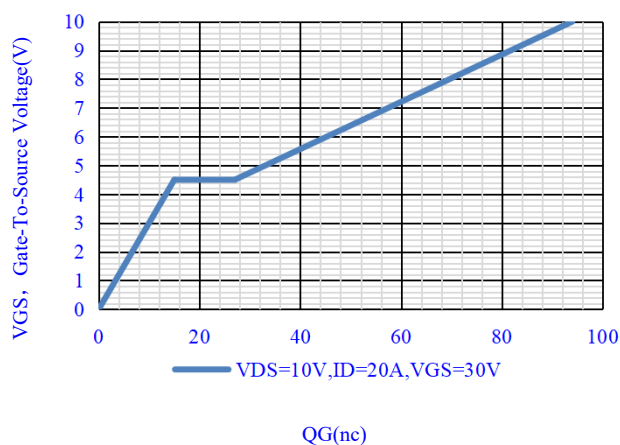


Fig.10-Gate Charge Waveform

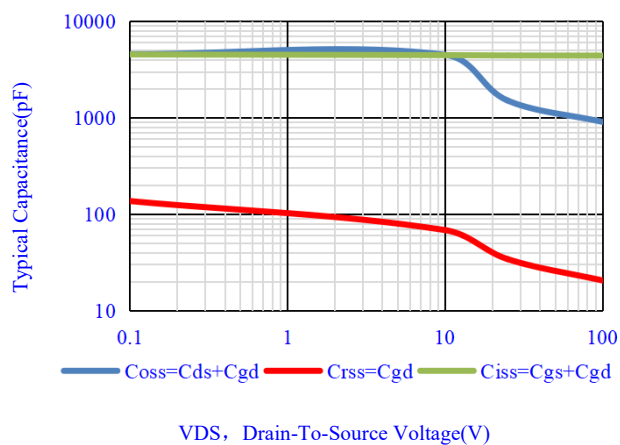


Fig.11-Typical Capacitance vs. Drain-To-Source Voltage

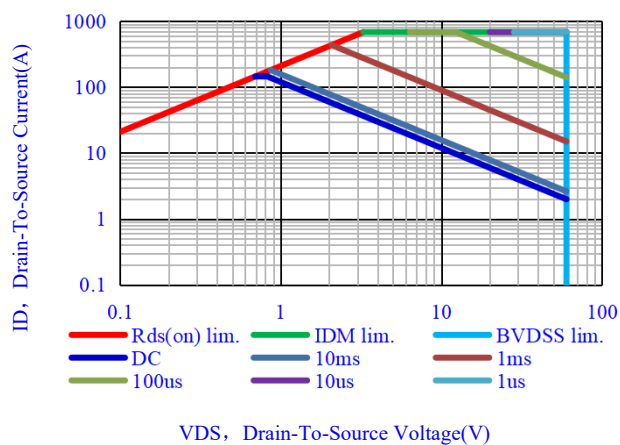


Fig.12-Maximum Safe Operating Area(SOA)

NSH020N06P5

N-Channel Enhanced Shielded Gate Trench Power MOSFET



Typical Characteristics Curves

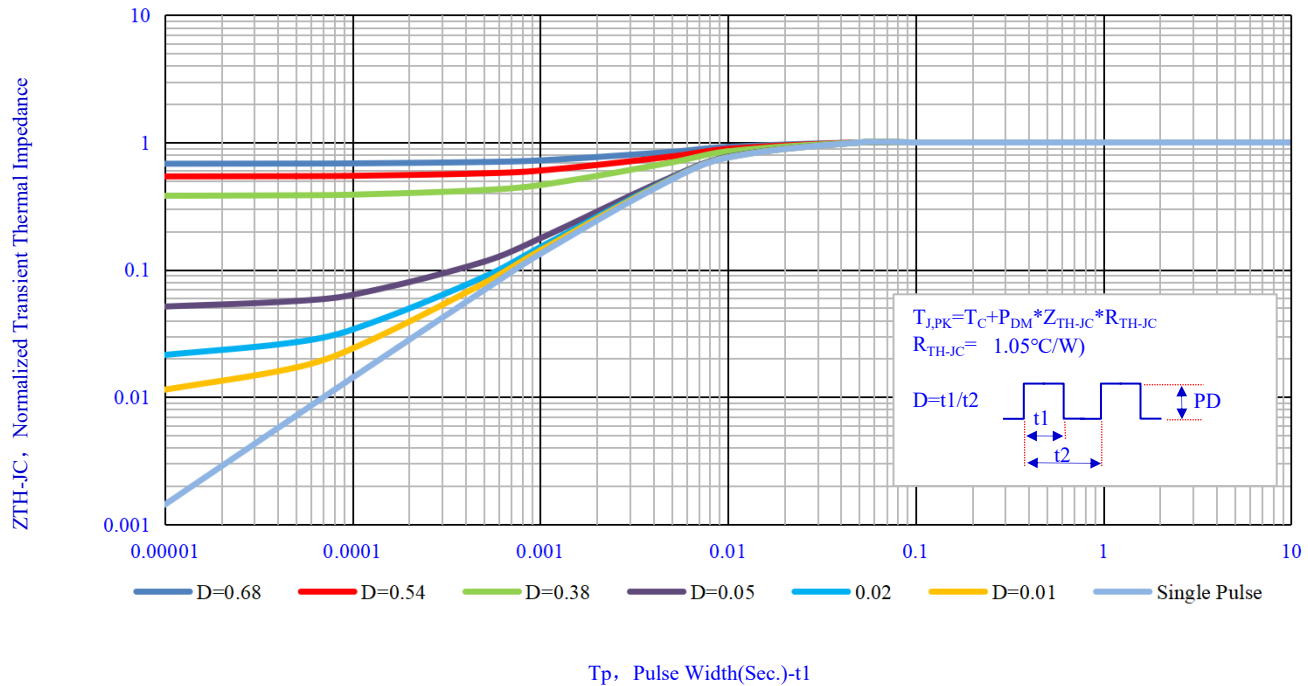


Fig.13- Normalized Maximum Transient Thermal Impedance vs.Pulse Width

Test Circuit & Waveform

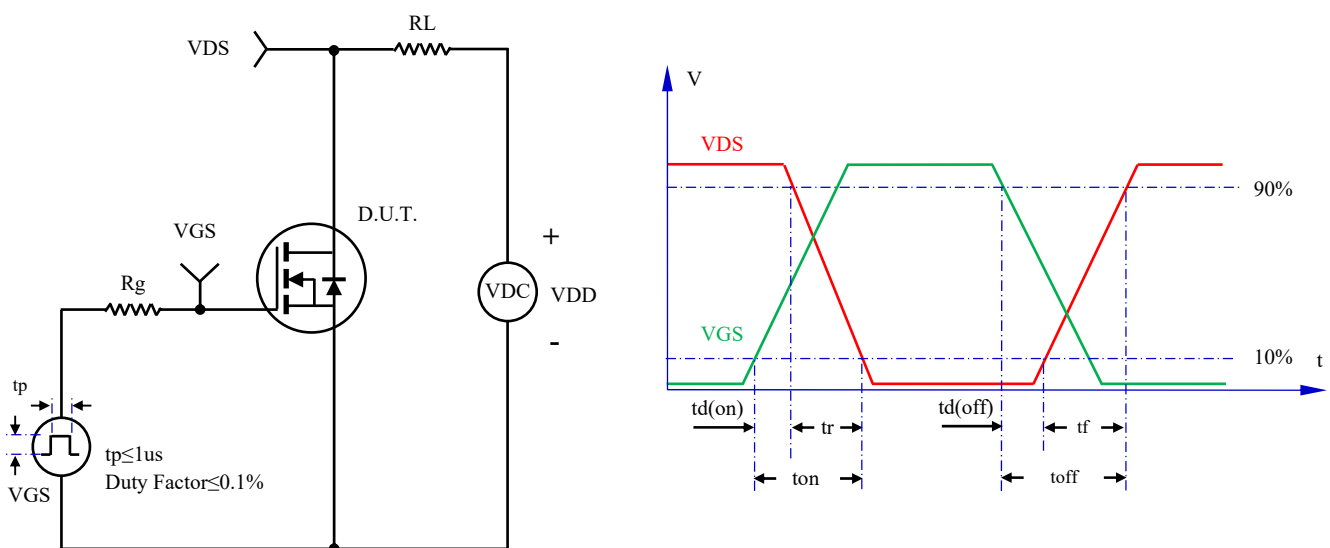


Fig.14- Resistive Switching Test Circuit & Waveform

NSH020N06P5

N-Channel Enhanced Shielded Gate Trench Power MOSFET



Test Circuit & Waveform

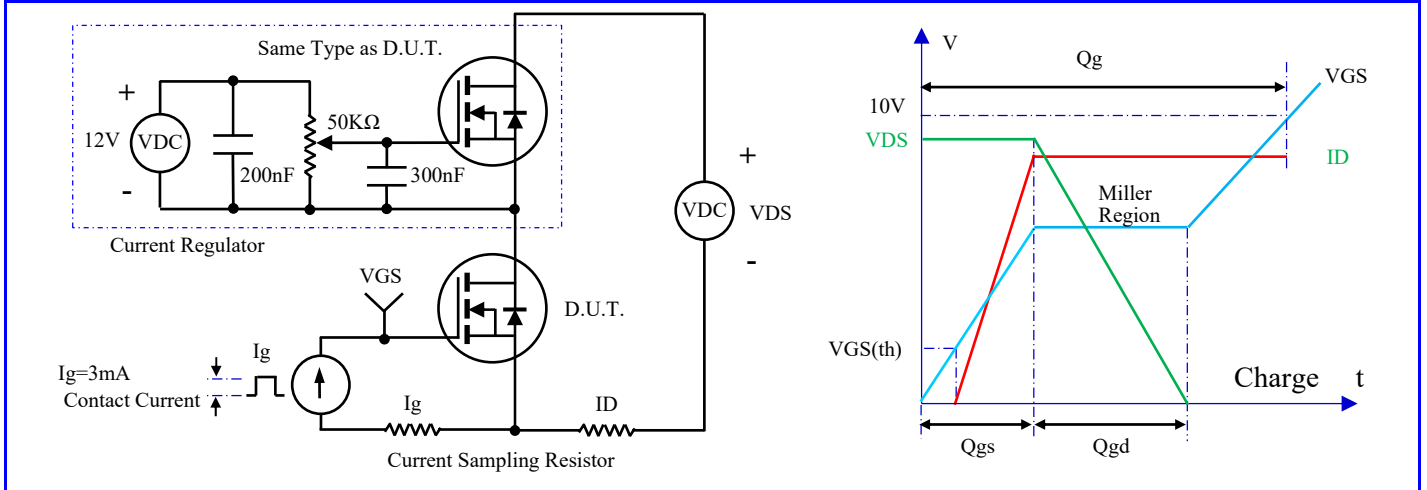


Fig.15- Gate Charge Test Circuit & Waveform

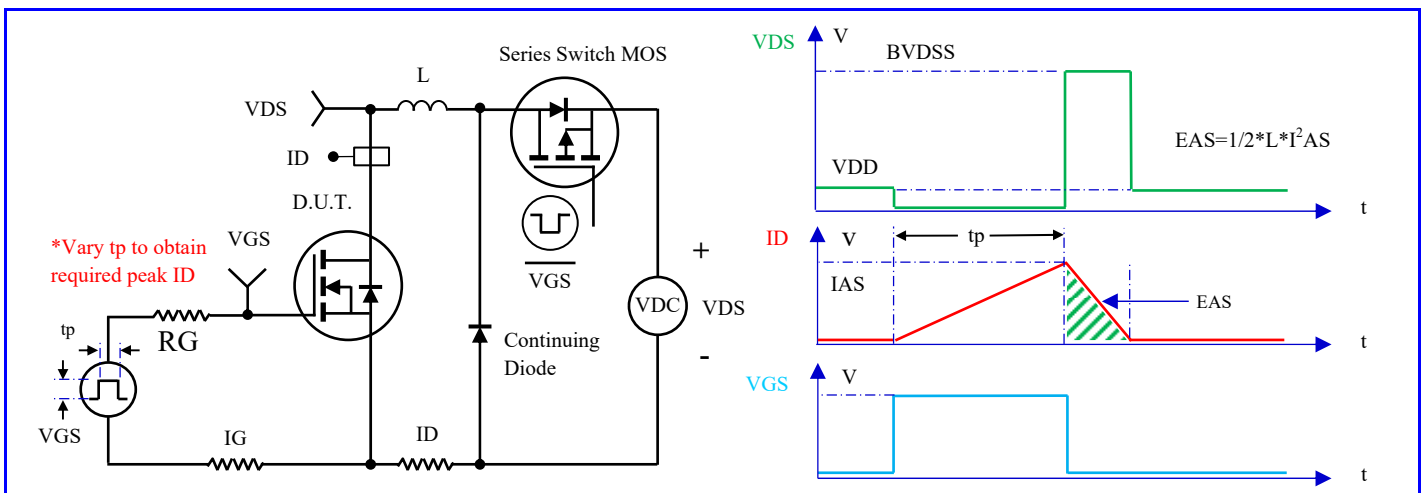


Fig.16- Unclamped Inductive Switching (UIS) Test Circuit & Waveform

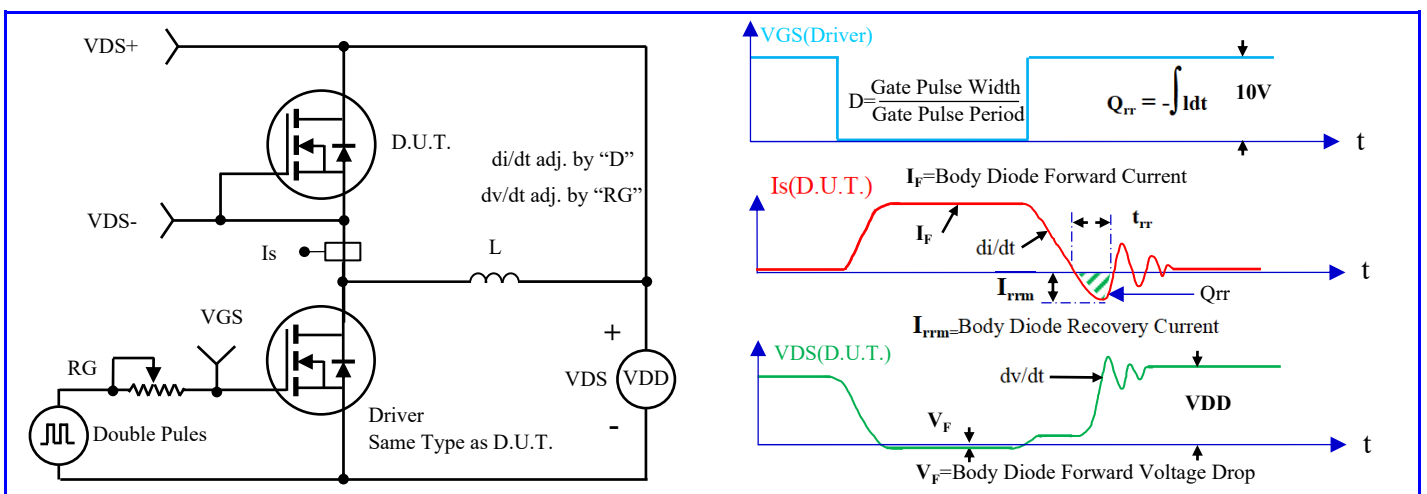


Fig.17- Diode Recovery Test Circuit & Waveform

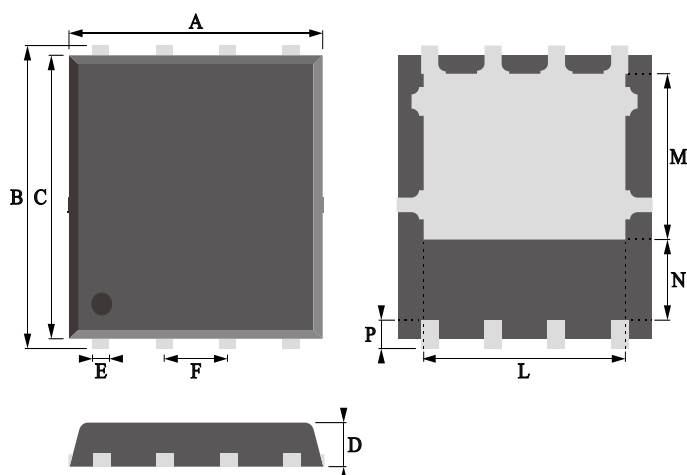
NSH020N06P5

N-Channel Enhanced Shielded Gate Trench Power MOSFET



OUTLINE DRAWINGS

PDFN5*6

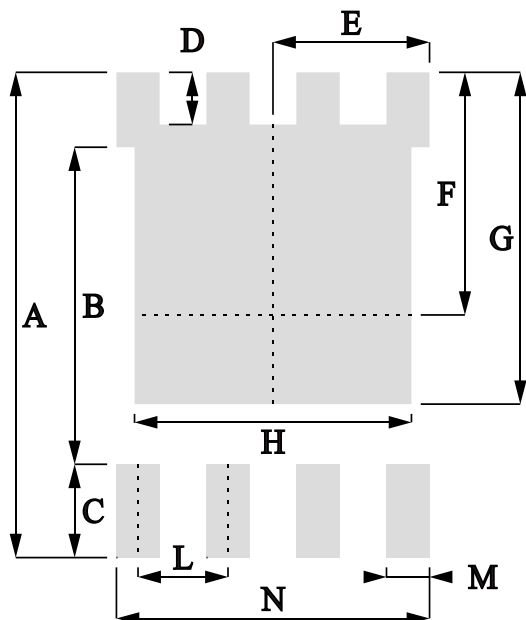


OUTLINE DIMENSIONS

Dim.	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.70	-	5.70	0.19	-	0.22
B	4.10	-	5.10	0.16	-	0.20
C	5.60	-	6.60	0.22	-	0.26
D	0.70	-	1.20	0.03	-	0.05
E	0.15	-	0.45	0.01	-	0.02
F	1.30	-	1.90	0.05	-	0.07
M	3.10	-	3.90	0.12	-	0.15
L	3.50	-	4.00	0.14	-	0.16
N	1.00	-	1.60	0.04	-	0.06
P	0.25	-	0.75	0.01	-	0.03

RECOMMEDNED LAYOUT DRAWINGS

PDFN5*6



OUTLINE DIMENSIONS

Dim.	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	-	6.61	-	-	0.26	-
B	-	4.32	-	-	0.17	-
C	-	1.27	-	-	0.05	-
D	-	0.71	-	-	0.03	-
E	-	2.21	-	-	0.09	-
F	-	3.31	-	-	0.13	-
G	-	4.52	-	-	0.18	-
H	-	3.91	-	-	0.15	-
L	-	1.27	-	-	0.05	-
M	-	0.61	-	-	0.02	-
N	-	4.42	-	-	0.17	-

PACKING INFORMATION

Package Code	Package Method	Min. Pack. Size (mm)	Quantity (Pcs/Min. Pack.)	Inner Box Size L×W×H(mm)	Quantity (Pcs/Inner Box)	Outer Carton Size L×W×H(mm)	Quantity (Pcs/Carton)
PDFN5*6	T/R	Φ330	2500	360×360×50	5000	380x380x340	30000

NSH020N06P5

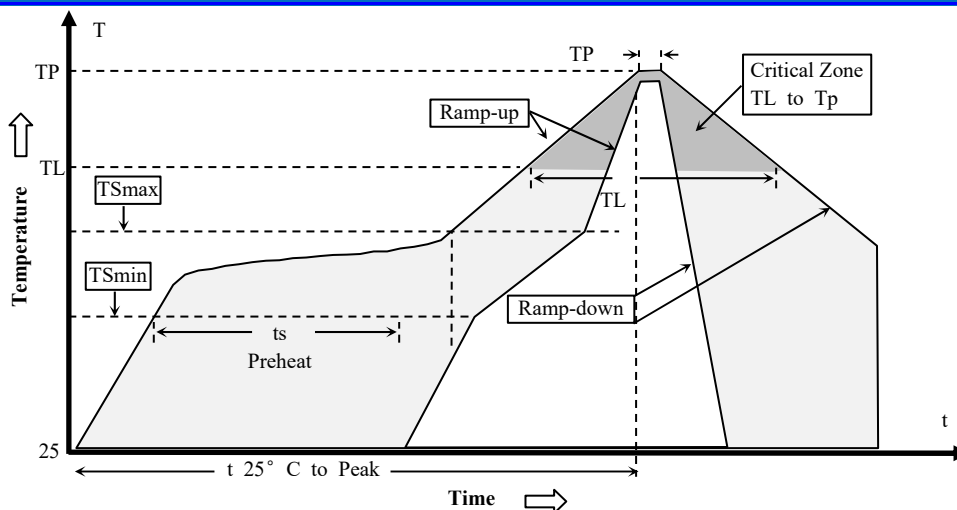
N-Channel Enhanced Shielded Gate Trench Power MOSFET



Recommended wave soldering condition

Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

Recommended temperature profile for IR reflow



Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (T _{smax} to T _p)	3°C/second max.	3°C/second max.
Preheat -Temperature Min(TS min) -Temperature Max(TS max) -Time(ts min to ts max)	100°C 150°C 60-120 seconds	150°C 200°C 60-180 seconds
Time maintained above: -Temperature (TL) - Time (tL)	183°C 60-150 seconds	217°C 60-150 seconds
Peak Temperature(TP)	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature(tp)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

Note : All temperatures refer to topside of the package, measured on the package body surface.

NSH020N06P5

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